NSN 5962-01-011-1339

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-011-1339

Body Length:

0.896 inches

Body Width:

Between 0.220 inches and 0.310 inches

Body Height:

Between 0.140 inches and 0.185 inches

Maximum Power Dissipation Rating:

525.0 milliwatts

Operating Tempurature Range:

+0.0/+70.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Hermetically sealed and monolithic and positive outputs and w/enable and programmable and programmed and high speed and w/open collector

Inclosure Material:

Ceramic and glass

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

10 input

Case Outline Source And Designator:

D-2 mil-m-38510

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

5.5 volts power source

Time Rating Per Chacteristic:

100.00 nanoseconds propagation delay time, low to high level output

Memory Device Type:

Rom

Test Data Document:

28480-a-1816-9002-1 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing,

etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

16 printed circuit

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

Yes - demil/mli

NSN 5962-01-011-1339

Memory Microcircuit - Page 2 of 2

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